

Michael Spencer

List of Publications by Year in descending order

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83
papers

3,126
citations

279778

23
h-index

155644

55
g-index

84
all docs

84
docs citations

84
times ranked

4892
citing authors

#	ARTICLE	IF	CITATIONS
1	Mechanical characterization of boron carbide single crystals. Journal of the American Ceramic Society, 2022, 105, 3030-3042.	3.8	8
2	High power direct energy conversion by nuclear batteries. Applied Physics Reviews, 2019, 6, 031305.	11.3	57
3	Synthesis of large area AB stacked bilayer graphene by SiC epitaxy and transfer. Nano Futures, 2018, 2, 035001.	2.2	5
4	High efficiency 4H-SiC betavoltaic power sources using tritium radioisotopes. Applied Physics Letters, 2016, 108, .	3.3	60
5	Simultaneous optical and electrical in vivo analysis of the enteric nervous system. Nature Communications, 2016, 7, 11800.	12.8	51
6	High frequency noise of epitaxial graphene grown on sapphire. Physica Status Solidi - Rapid Research Letters, 2013, 7, 348-351.	2.4	5
7	Surface modification of porous alumina membranes by collagen layers: Performance and characterization. Separation and Purification Technology, 2013, 115, 114-122.	7.9	12
8	Electrically tunable molecular doping of graphene. Applied Physics Letters, 2013, 102, .	3.3	77
9	Correlated conductivity and work function changes in epitaxial graphene. Applied Physics Letters, 2012, 100, .	3.3	30
10	Chemical vapor deposition of graphene on copper at reduced temperatures. Proceedings of SPIE, 2012, , .	0.8	2
11	Very Slow Cooling Dynamics of Photoexcited Carriers in Graphene Observed by Optical-Pump Terahertz-Probe Spectroscopy. Nano Letters, 2011, 11, 4902-4906.	9.1	170
12	Oriented 2D Covalent Organic Framework Thin Films on Single-Layer Graphene. Science, 2011, 332, 228-231.	12.6	997
13	Very Slow Carrier Cooling in Graphene Measured by Optical/THz Pump-Probe Spectroscopy. , 2011, , .		0
14	Highly sensitive and selective NO. , 2010, , .		4
15	High intensity red emission from Eu doped GaN powders. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1495-1498.	0.8	8
16	High breakdown voltage AlGaIn/GaN heterojunction field effect transistors on sapphire. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2013-2015.	0.8	7
17	Development and Validation of a Prognostic Index for Health Outcomes in Chronic Obstructive Pulmonary Disease. Archives of Internal Medicine, 2008, 168, 71.	3.8	78
18	High breakdown voltage C-doped GaN-on-sapphire HFETs with a low specific on-resistance. Semiconductor Science and Technology, 2007, 22, 517-521.	2.0	26

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19	Electronic properties of a 3C ⁺ 4H SiC polytype heterojunction formed on the Si face. Applied Physics Letters, 2007, 90, 173509.	3.3	23
20	High Breakdown Voltage and Low Specific On-resistance C-doped GaN-on-sapphire HFETs for Low-loss and High-power Switching Applications. , 2007, , .		3
21	Field Demonstration of Visible Opacity Photographic Systems. Journal of the Air and Waste Management Association, 2007, 57, 31-38.	1.9	3
22	C-doped semi-insulating GaN HFETs on sapphire substrates with a high breakdown voltage and low specific on-resistance. Journal of Vacuum Science & Technology B, 2007, 25, 1836.	1.3	23
23	GaN ballistic negative-differential-conductivity diode for potential THz applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 528-530.	0.8	2
24	Characterization of bulk grown GaN and AlN single crystal materials. Journal of Crystal Growth, 2006, 287, 349-353.	1.5	20
25	Demonstration of a 4H SiC betavoltaic cell. Applied Physics Letters, 2006, 88, 033506.	3.3	124
26	Ohmic contact using the Si nano-interlayer for undoped-AlGa ⁺ N/GaN heterostructures. Journal of Electronic Materials, 2006, 35, 406-410.	2.2	8
27	Fabrication and characterization of high breakdown voltage AlGa ⁺ N ⁺ -GaN heterojunction field effect transistors on sapphire substrates. Journal of Vacuum Science & Technology B, 2006, 24, 2601.	1.3	26
28	Influence of low-field-mobility-related issues on SiC metal-semiconductor field-effect transistor performance. Journal of Electronic Materials, 2005, 34, 330-335.	2.2	8
29	Influence of Small Doses of Gamma Irradiation on Transport and Noise Properties of SiC MESFETs. AIP Conference Proceedings, 2005, , .	0.4	0
30	Nanoscale Capacitance-Voltage Characterization of Two-Dimensional Electron Gas in AlGa ⁺ N/GaN Heterostructures. Japanese Journal of Applied Physics, 2005, 44, L1348-L1351.	1.5	5
31	On the origin of the two-dimensional electron gas at the AlGa ⁺ N ⁺ -GaN heterostructure interface. Applied Physics Letters, 2005, 86, 042107.	3.3	108
32	Hot-electron transport in 4H ⁺ SiC. Applied Physics Letters, 2005, 86, 022107.	3.3	13
33	Rapid growth of bulk GaN crystal using GaN powder as source material. Materials Research Society Symposia Proceedings, 2005, 892, 684.	0.1	3
34	Structural characterization of GaN single crystal layers grown by vapor transport from a gallium oxide (Ga ₂ O ₃) powder source. Materials Research Society Symposia Proceedings, 2005, 892, 708.	0.1	0
35	Perturbation of charges in AlGa ⁺ N ⁺ -GaN heterostructures by ultraviolet laser illumination. Journal of Applied Physics, 2004, 96, 4253-4262.	2.5	14
36	Hot-phonon temperature and lifetime in biased 4H-SiC. Journal of Applied Physics, 2004, 96, 6439-6444.	2.5	26

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37	X-ray characterization of GaN single crystal layers grown by the ammonothermal technique on HVPE GaN seeds and by the sublimation technique on sapphire seeds. Materials Research Society Symposia Proceedings, 2004, 831, 55.	0.1	0
38	Influence of Si ₃ N ₄ passivation on surface trapping in SiC metal-semiconductor field-effect transistors. Journal of Electronic Materials, 2004, 33, 908-911.	2.2	2
39	3C-SiC modulator for high-speed integrated photonics. Materials Research Society Symposia Proceedings, 2003, 799, 158.	0.1	2
40	Laser-induced surface potential transients observed in III-nitride heterostructures. Applied Physics Letters, 2002, 81, 2282-2284.	3.3	16
41	A comparison of graphite and AlN caps used for annealing ion-implanted SiC. Journal of Electronic Materials, 2002, 31, 568-575.	2.2	11
42	Scanning Kelvin probe microscopy characterization of dislocations in III-nitrides grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 78, 2873-2875.	3.3	69
43	Characterization of GaN and Al _{0.35} Ga _{0.65} N/GaN Heterostructures by Scanning Kelvin Probe Microscopy. Materials Research Society Symposia Proceedings, 2001, 680, 1.	0.1	0
44	Modification of Indium Tin Oxide for Improved Hole Injection in Organic Light Emitting Diodes. Advanced Materials, 2001, 13, 1234.	21.0	99
45	Surface potential measurements on GaN and AlGaN/GaN heterostructures by scanning Kelvin probe microscopy. Journal of Applied Physics, 2001, 90, 337-344.	2.5	130
46	SiC/Si(111) film quality as a function of GeH ₄ flow in an MOCVD reactor. Journal of Electronic Materials, 2000, 29, 359-363.	2.2	4
47	An SEM Investigation of Annealing Encapsulants for SiC. Microscopy and Microanalysis, 2000, 6, 1094-1095.	0.4	0
48	Comparative Growth of AlN on Singular and Off-Axis 6H and 4H-SiC by MOCVD. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 344-350.	1.0	0
49	Homo-Epitaxial and Selective Area Growth of 4H and 6H Silicon Carbide Using a Resistively Heated Vertical Reactor. Materials Research Society Symposia Proceedings, 1999, 572, 173.	0.1	6
50	Effect of Ge on SiC Film Morphology in SiC/Si Films Grown by MOCVD. Materials Research Society Symposia Proceedings, 1999, 572, 185.	0.1	0
51	Investigation of the Morphology of AlN Films Grown on Sapphire by MOCVD Using Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 1999, 572, 339.	0.1	0
52	Annealing of Ion Implantation Damage in SiC Using a Graphite Mask. Materials Research Society Symposia Proceedings, 1999, 572, 45.	0.1	11
53	Heteroepitaxy of ZnO on GaN and its implications for fabrication of hybrid optoelectronic devices. Applied Physics Letters, 1998, 73, 348-350.	3.3	425
54	Comparative Growth of AlN on Singular and Off-Axis 6H and 4H-SiC by MOCVD. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	0

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55	Investigation of aluminum nitride grown by metal-organic chemical-vapor deposition on silicon carbide. Journal of Applied Physics, 1997, 82, 2990-2995.	2.5	65
56	Pulsed Laser Deposition of Highly Crystalline GaN Films on Sapphire. Materials Research Society Symposia Proceedings, 1997, 482, 410.	0.1	2
57	Formation and High Frequency CV-Measurements of Aluminum / Aluminum Nitride / 6H Silicon Carbide Structures. Materials Research Society Symposia Proceedings, 1996, 423, 667.	0.1	14
58	Comparison of the Microstructure of AlN Films Grown by MOCVD and by PLD on Sapphire Substrates. Materials Research Society Symposia Proceedings, 1996, 449, 453.	0.1	1
59	Structural Characteristics of MOCVD Grown AlN Films with Different Carbon Concentration. Materials Research Society Symposia Proceedings, 1996, 449, 555.	0.1	1
60	Low Resistivity Aluminum Nitride: Carbon (AlN:C) Films Grown by Metal Organic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1995, 395, 279.	0.1	2
61	Cubic SiC the Forgotten Polytype. Materials Research Society Symposia Proceedings, 1995, 410, 329.	0.1	5
62	Low resistivity as-deposited ohmic contacts to 3C-SiC. Journal of Electronic Materials, 1995, 24, 315-318.	2.2	15
63	Identification of the neutral V ⁴⁺ -impurity in cubic 3C-SiC by electron-spin resonance and optically detected magnetic resonance. Physical Review B, 1994, 50, 18034-18039.	3.2	14
64	Defect assisted tunneling in GaAs/AlGaAs/GaAs heterostructures. Journal of Applied Physics, 1994, 75, 368-372.	2.5	3
65	Deep donor state of vanadium in cubic silicon carbide (3C-SiC). Applied Physics Letters, 1994, 65, 1811-1813.	3.3	34
66	Structural Study of SiC/AlN Bilayers and Trilayers on Si and 6H-SiC. Materials Research Society Symposia Proceedings, 1994, 339, 363.	0.1	1
67	Electron tunneling spectroscopy and defects in GaAs/AlGaAs/GaAs heterostructures. Journal of Applied Physics, 1992, 72, 5333-5336.	2.5	3
68	Heteropolytype Growth of Beta Silicon Carbide on Alpha Silicon Carbide by Low Pressure Chemical Vapor Deposition at 1150 C. Materials Research Society Symposia Proceedings, 1992, 281, 793.	0.1	0
69	Optically detected magnetic resonance of group-IV and group-VI impurities in AlAs and Al _x Ga _{1-x} As with x ≈ 0.35. Physical Review B, 1991, 43, 14540-14556.	3.2	19
70	Enhanced photoemission from a bi-metallic LaB ₆ /Au photocathode structure. Applied Physics Letters, 1991, 58, 1795-1796.	3.3	1
71	Second harmonic conversion in cubic silicon carbide at 1.06 μm. Applied Physics Letters, 1991, 59, 1817-1819.	3.3	7
72	Increase of electrical activation and mobility of Si-doped GaAs, grown at low substrate temperatures, by the migration-enhanced epitaxy method. Journal of Applied Physics, 1990, 67, 589-591.	2.5	8

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73	A novel method for the growth of good quality GaAs at extremely low substrate temperatures (as) Tj ETQq1 1 0.784314 rgBT /Overlook Society B, Microelectronics Processing and Phenomena, 1990, 8, 131.	1.6	4
74	Reduction of Be diffusion in GaAs by migration-enhanced epitaxy. Applied Physics Letters, 1989, 55, 59-61.	3.3	9
75	Symmetry of the Si shallow donor state in AlAs/GaAs and Al _x Ga _{1-x} As/GaAs heterostructures. Physical Review B, 1989, 40, 3447-3450.	3.2	28
76	Metastable defects in Be-doped Al _x Ga _{1-x} As. Journal of Applied Physics, 1989, 65, 4828-4831.	2.5	0
77	Beryllium Doping in MBE-grown GaAs and AlGaAs. Materials Research Society Symposia Proceedings, 1989, 163, 881.	0.1	0
78	Optically detected magnetic resonance of native defects in Al _x Ga _{1-x} As. Physical Review B, 1988, 37, 6325-6331.	3.2	26
79	Growth of GaAs-AlGaAs by migration-enhanced epitaxy. Applied Physics Letters, 1988, 53, 2664-2665.	3.3	13
80	Observation of optically detected magnetic resonance signals in Al _x Ga _{1-x} As. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 762.	1.6	5
81	Beta Silicon Carbide Growth with Device Applications. Materials Research Society Symposia Proceedings, 1987, 97, 201.	0.1	0
82	Observation of deep levels in cubic silicon carbide. Applied Physics Letters, 1987, 50, 1384-1385.	3.3	40
83	Characterization of grain boundaries using deep level transient spectroscopy. Journal of Applied Physics, 1979, 50, 8006-8009.	2.5	25